

IPP65R110CFDXKSA1

IPP65R110CFDXKSA1 Information



For Reference Only

Part Number IPP65R110CFDXKSA1
Manufacturer Infineon Technologies

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 700V 31.2A TO220

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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IPP65R110CFDXKSA1 Specifications

Manufacturer Part Number IPP65R110CFDXKSA1 Manufacturer Infineon Technologies Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Series CoolMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 700V Current - Continuous Drain (Id) @ 25°C 31.2A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4.5V @ 1.3mA Gate Charge (Qg) (Max) @ Vgs 118nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 3240pF @ 100V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 277.8W (Tc) Rds On (Max) @ Id, Vgs 110 mOhm @ 12.7A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO-220-3 Package / Case TO-220-3 Report errors?		
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Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 31.2A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 4.5V @ 1.3mA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 110 mOhm @ 12.7A, 10V Operating Temperature Supplier Device Package PG-TO-220-3 Package / Case TO-220-3	Series	CoolMOS?
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Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 4.5V @ 1.3mA Gate Charge (Qg) (Max) @ Vgs 118nC @ 10V Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 110 mOhm @ 12.7A, 10V Operating Temperature Supplier Device Package PG-TO-220-3 Package / Case 31.2A (Tc) 10V 4.5V @ 1.3mA 3240pF @ 100V 420V Though (Tc) Though Hole Supplier Device Package PG-TO-220-3 TO-220-3	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 4.5V @ 1.3mA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 110 mOhm @ 12.7A, 10V Operating Temperature Supplier Device Package PG-TO-220-3 Package / Case 10V 4.5V @ 1.3mA 118nC @ 10V 1290 1200 1	Drain to Source Voltage (Vdss)	700V
Vgs(th) (Max) @ Id 4.5V @ 1.3mA Gate Charge (Qg) (Max) @ Vgs 118nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 3240pF @ 100V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 277.8W (Tc) Rds On (Max) @ Id, Vgs 110 mOhm @ 12.7A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO-220-3 Package / Case TO-220-3	Current - Continuous Drain (Id) @ 25°C	31.2A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) +20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 110 mOhm @ 12.7A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO-220-3 Package / Case TO-220-3	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) E20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 110 mOhm @ 12.7A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO-220-3 Package / Case TO-220-3	Vgs(th) (Max) @ Id	4.5V @ 1.3mA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)277.8W (Tc)Rds On (Max) @ Id, Vgs110 mOhm @ 12.7A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePG-TO-220-3Package / CaseTO-220-3	Gate Charge (Qg) (Max) @ Vgs	118nC @ 10V
FET Feature - Power Dissipation (Max) 277.8W (Tc) Rds On (Max) @ Id, Vgs 110 mOhm @ 12.7A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO-220-3 Package / Case TO-220-3	Input Capacitance (Ciss) (Max) @ Vds	3240pF @ 100V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 110 mOhm @ 12.7A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO-220-3 Package / Case TO-220-3	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs 110 mOhm @ 12.7A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO-220-3 Package / Case TO-220-3	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO-220-3 Package / Case TO-220-3	Power Dissipation (Max)	277.8W (Tc)
Mounting Type Through Hole Supplier Device Package PG-TO-220-3 Package / Case TO-220-3	Rds On (Max) @ Id, Vgs	110 mOhm @ 12.7A, 10V
Supplier Device Package PG-TO-220-3 Package / Case TO-220-3	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-220-3	Mounting Type	Through Hole
	Supplier Device Package	PG-TO-220-3
Report errors?	Package / Case	TO-220-3
		Report errors?

IPP65R110CFDXKSA1 Guarantees



Ouality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IPP65R110CFDXKSA1 Payment Methods

































If you have any question about IPP65R110CFDXKSA1, please do not hesitate to contact us!

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